

- 1N4150-1 AVAILABLE IN JAN, JANTX, AND JANTXV PER MIL-PRF-19500/231
- 1N3600 AVAILABLE IN JAN, JANTX, AND JANTXV PER MIL-PRF-19500/231
- SWITCHING DIODES
- HERMETICALLY SEALED
- METALLURGICALLY BONDED
- DOUBLE PLUG CONSTRUCTION

**1N4150
and
1N4150-1
and
1N3600**

MAXIMUM RATINGS

Junction Temperature: -65°C to +175°C

Storage Temperature: -65°C to +175°C

Operating Current: 300 mA @ $T_A = +25^\circ\text{C}$

Derating: 2.0 mA dc/°C Above $T_L = +75^\circ\text{C}$ @ $L = 3/8"$

Forward Surge Current: 4A, (tp = 1μs); 0.5A (tp = 1s)

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified.

Type	V_{BR}	V_{RWM}	I_{R1} $V_R = 50\text{ V dc}$ $T_A = 25^\circ\text{C}$	I_{R2} $V_R = 50\text{ V dc}$ $T_A = 150^\circ\text{C}$	C $V_R = 0$; $f = 1\text{ Mhz}$; ac signals = 50 mV (p-p)	t_{rr} $I_F = I_R = 10\text{ to }100\text{ mA dc}$ $R_L = 100\text{ ohms}$
	$I_R = 10\text{ }\mu\text{A}$					
	V dc	V (pk)	μA dc	μA dc	pF	ns
1N3600	75	50	0.1	100	2.5	4
1N4150,-1	75	50	0.1	100	2.5	4

FORWARD VOLTAGE LIMITS – ALL TYPES

Limits	V_{F1} $I_F = 1\text{ mA dc}$	V_{F2} $I_F = 10\text{ mA dc}$	V_{F3} $I_F = 50\text{ mA dc}$ (Pulsed)	V_{F4} $I_F = 100\text{ mA dc}$ (Pulsed)	V_{F5} $I_F = 200\text{ mA dc}$ (Pulsed)
	V dc	V dc	V dc	V dc	V dc
minimum	0.540	0.660	0.760	0.820	0.870
maximum	0.620	0.740	0.860	0.920	1.000

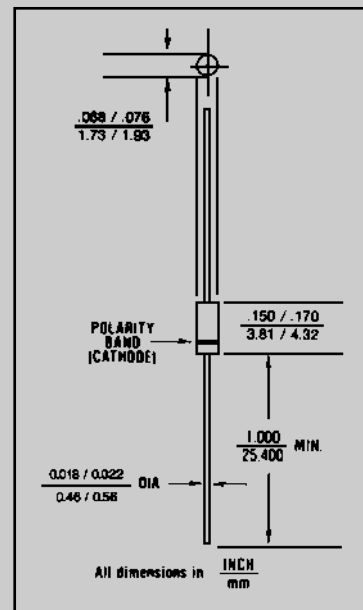


FIGURE 1

DESIGN DATA

CASE: Hermetically sealed glass case per MIL-S-19500/231 D0-35 outline.

LEAD MATERIAL: Copper clad steel.

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: ($R_{\theta JL}$): 250 °C/W maximum at $L = .375$

THERMAL IMPEDANCE: ($Z_{\theta JX}$): 70 °C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: Any.



IN4150, IN4150-1 and IN3600

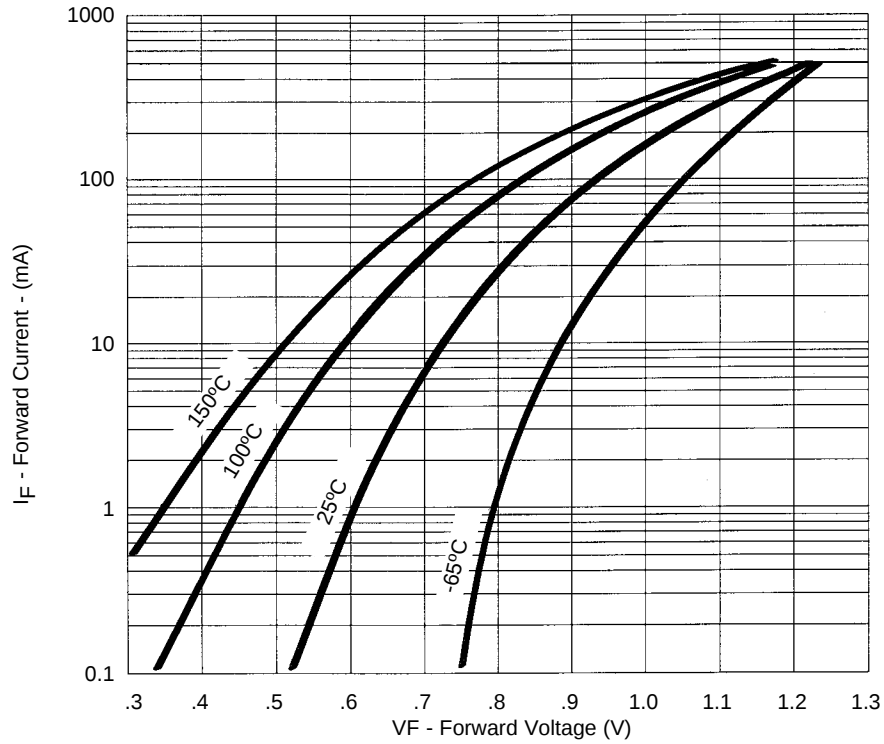
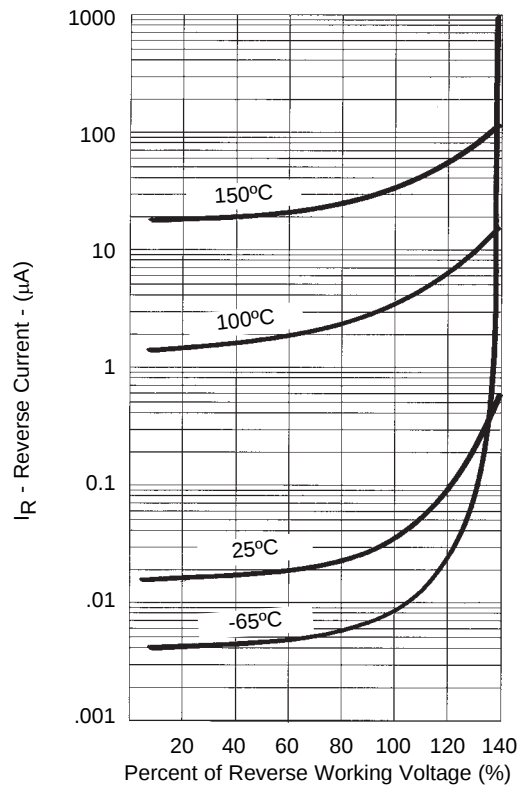


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage